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# MOSFET – Power, Dual, N-Channel, for 1-Cell Lithium-ion Battery Protection

# 12 V, 2.85 mΩ, 20 A

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1–cell lithium-ion battery applications.

#### **Features**

- 2.5 V Drive
- Common-Drain Type
- ESD Diode-Protected Gate
- This device is Pb-Free, Halogen Free and RoHS Compliance

#### **Applications**

• 1-Cell Lithium-ion Battery Charging and Discharging Switch

#### **Specifications**

#### ABSOLUTE MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Parameter	Symbol	Value	Unit
Source to Source Voltage	V <sub>SSS</sub>	12	V
Gate to Source Voltage	V <sub>GSS</sub>	±8	V
Source Current (DC)	I <sub>S</sub>	20	Α
Source Current (Pulse) PW ≤ 10 μs, duty cycle ≤ 1%	I <sub>SP</sub>	80	Α
Total Dissipation (Note 1)	P <sub>T</sub>	1.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{\theta JA}$	69.4	°C/W

<sup>1.</sup> Surface mounted on ceramic substrate (5000 mm<sup>2</sup> × 0.8 mm).

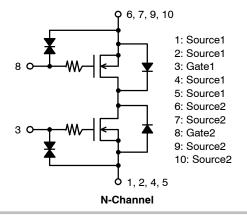


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V <sub>SSS</sub>	R <sub>SS(ON)</sub> MAX	I <sub>S</sub> MAX
12 V	2.85 m $\Omega$ @ 4.5 V	20 A
	3.1 mΩ @ 3.8 V	
	4.7 mΩ @ 3.1 V	
	6.8 mΩ @ 2.5 V	

#### **ELECTRICAL CONNECTION**



#### **PIN ASSIGNMENT**



WLCSP10 (1.84 x 1.96 x 0.13) CASE 567VW



#### **MARKING DIAGRAM**



NY = Specific Device Code A = Assembly Location

Y = Year W = Work Week ZZ = Assembly Lot

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** $(T_A = 25^{\circ}C)$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)SSS</sub>	Source to Source Breakdown Voltage	I <sub>S</sub> = 1 mA, V <sub>GS</sub> = 0 V	12			V
I <sub>SSS</sub>	Zero-Gate Voltage Source Current	V <sub>SS</sub> = 10 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$			±1	μΑ
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>SS</sub> = 6 V, I <sub>S</sub> = 1 mA	0.4		1.3	V
R <sub>SS</sub> (on) Static Source to Source On-S Resistance	Static Source to Source On-State	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 4.5 V	1.5	2.2	2.85	mΩ
	Hesistance	I <sub>S</sub> = 5 A, V <sub>GS</sub> = 3.8 V	1.65	2.4	3.1	mΩ
		I <sub>S</sub> = 5 A, V <sub>GS</sub> = 3.1 V	1.9	2.8	4.7	mΩ
		I <sub>S</sub> = 5 A, V <sub>GS</sub> = 2.5 V	2.0	3.3	6.8	mΩ
t <sub>d</sub> (on)	Turn-ON Delay Time	V <sub>SS</sub> = 5 V, V <sub>GS</sub> = 3.8 V, I <sub>S</sub> = 5 A		11		μs
t <sub>r</sub>	Rise Time	Rg = 10 kΩ Switching Test Circuit		36		μs
t <sub>d</sub> (off)	Turn-OFF Delay Time	]		95		μs
t <sub>f</sub>	Fall Time	1		70		μs
Qg	Total Gate Charge	V <sub>SS</sub> = 5 V, V <sub>GS</sub> = 3.8 V, I <sub>S</sub> = 5 A		30		nC
$V_{F(S-S)}$	Forward Source to Source Voltage	I <sub>S</sub> = 3 A, V <sub>GS</sub> = 0 V		0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

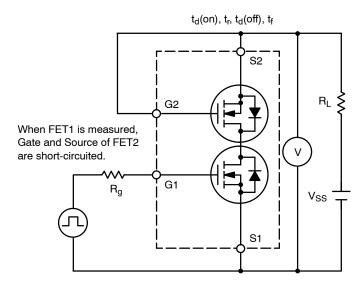


Figure 1. Switching Test Circuit

#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup> (Qty / Packing)
EFC2K107NUZTCG	NY	WLCSOP10, 1.84 x 1.96 x 0.13 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **TYPICAL CHARACTERISTICS**

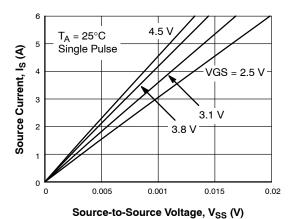


Figure 2. On-Region Characteristics

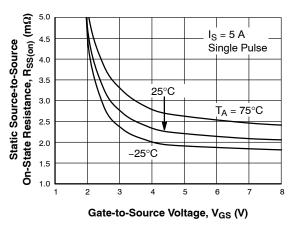


Figure 4. On-Resistance vs. Gate-to-Source Voltage

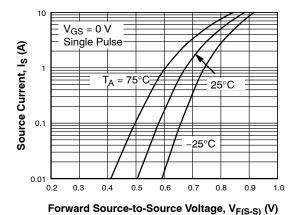


Figure 6. Forward Source-to-Source Voltage vs. Current

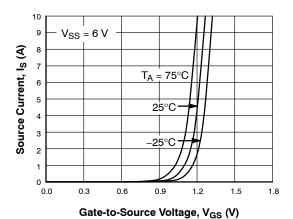


Figure 3. Transfer Characteristics

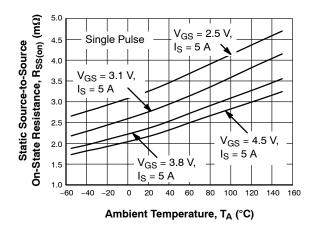


Figure 5. On-Resistance vs. Temperature

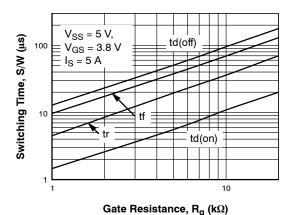


Figure 7. Switching Time vs. Gate Resistance

#### **TYPICAL CHARACTERISTICS**

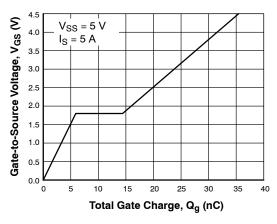


Figure 8. Gate-to-Source Voltage vs. Total Charge

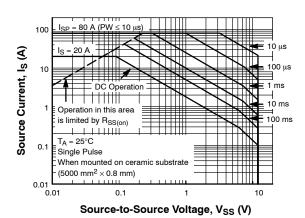


Figure 9. Safe Operating Area

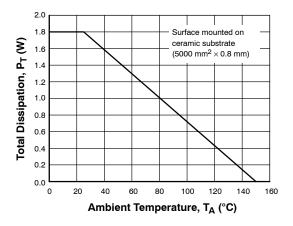


Figure 10. Total Dissipation vs. Temperature

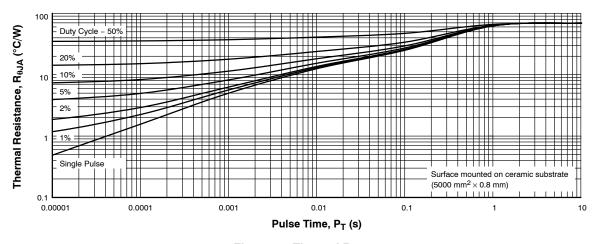
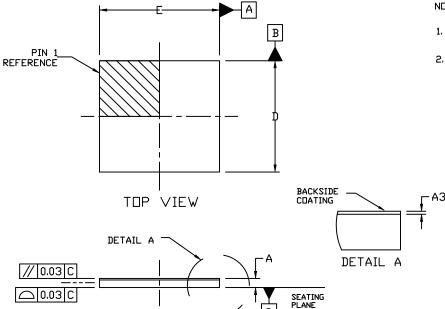


Figure 11. Thermal Response

Note on Usage: Since the EFC2K107NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

### WLCSP10 1.84x1.96x0.13 CASE 567VW ISSUE O

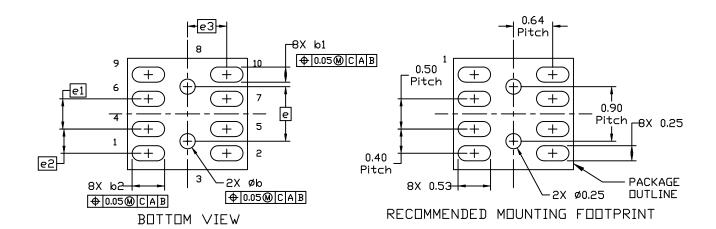
**DATE 28 FEB 2018** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	0.10	0.125	0.15	
A3	0.025 REF			
b	0.22	0.25	0.28	
b1	0.22	0.25	0.28	
b2	0.50	0.53	0.56	
D	1.81	1.84	1.87	
E	1.93	1.96	1.99	
е	0.90 BSC			
e1	0.50 BSC			
e2	0.40 BSC			
e3	0.64 BSC			



# GENERIC MARKING DIAGRAM\*

SIDE VIEW

XXXXXX AYWZZ

A = Assembly Location

Y = Year W = Work WeekZZ = Assembly Lot \*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	WLCSP10 1.84x1.96x0.13		PAGE 1 OF 1	

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